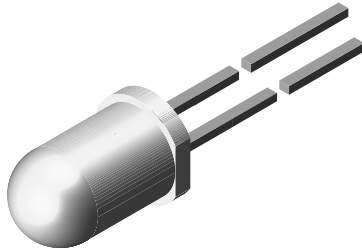


## Infrared Emitting Diode, 875 nm, GaAlAs



94 8389

### FEATURES

- Package type: leaded
- Package form: T-1 $\frac{3}{4}$
- Dimensions (in mm):  $\varnothing$  5
- Peak wavelength:  $\lambda_p = 875$  nm
- High reliability
- Angle of half intensity:  $\varphi = \pm 12^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- Good spectral matching with Si photodetectors
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

### DESCRIPTION

The TSHA620. series are infrared, 875 nm emitting diodes in GaAlAs technology, molded in a clear, untinted plastic package.

### APPLICATIONS

- Infrared remote control and free air data transmission systems
- This emitter series is dedicated to systems with panes in transmission space between emitter and detector, because of the low absorption of 875 nm radiation in glass

### PRODUCT SUMMARY

COMPONENT	$I_e$ (mW/sr)	$\varphi$ (deg)	$\lambda_p$ (nm)	$t_r$ (ns)
TSHA6200	40	$\pm 12$	875	600
TSHA6201	50	$\pm 12$	875	600
TSHA6202	60	$\pm 12$	875	600
TSHA6203	65	$\pm 12$	875	600

#### Note

Test conditions see table "Basic Characteristics"

### ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TSHA6200	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1 $\frac{3}{4}$
TSHA6201	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1 $\frac{3}{4}$
TSHA6202	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1 $\frac{3}{4}$
TSHA6203	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1 $\frac{3}{4}$

#### Note

MOQ: minimum order quantity

### ABSOLUTE MAXIMUM RATINGS

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		$V_R$	5	V
Forward current		$I_F$	100	mA
Peak forward current	$t_p/T = 0.5, t_p = 100 \mu s$	$I_{FM}$	200	mA
Surge forward current	$t_p = 100 \mu s$	$I_{FSM}$	2.5	A
Power dissipation		$P_V$	180	mW
Junction temperature		$T_j$	100	$^\circ C$
Operating temperature range		$T_{amb}$	- 40 to + 85	$^\circ C$
Storage temperature range		$T_{stg}$	- 40 to + 100	$^\circ C$
Soldering temperature	$t \leq 5$ s, 2 mm from case	$T_{sd}$	260	$^\circ C$
Thermal resistance junction/ambient	J-STD-051, leads 7 mm, soldered on PCB	$R_{thJA}$	230	K/W

#### Note

$T_{amb} = 25 \text{ }^\circ C$ , unless otherwise specified

# TSHA6200, TSHA6201, TSHA6202, TSHA6203

Vishay Semiconductors Infrared Emitting Diode, 875 nm, GaAlAs

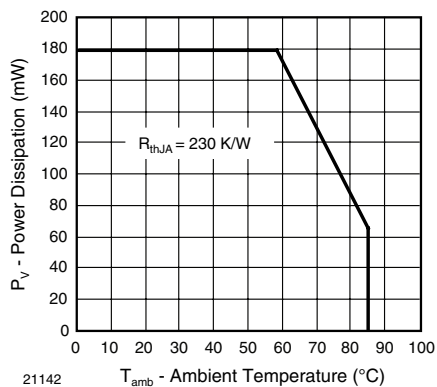


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

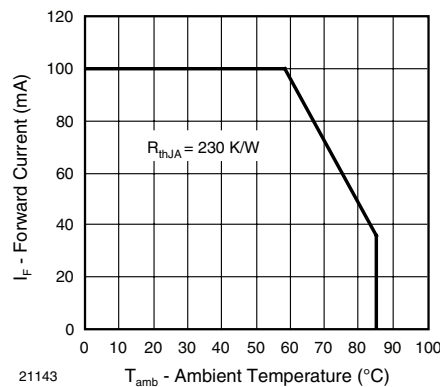


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms	V <sub>F</sub>		1.5	1.8	V
Temperature coefficient of V <sub>F</sub>	I <sub>F</sub> = 100 mA	TK <sub>V<sub>F</sub></sub>		- 1.6		mV/K
Reverse current	V <sub>R</sub> = 5 V	I <sub>R</sub>			100	μA
Junction capacitance	V <sub>R</sub> = 0 V, f = 1 MHz, E = 0	C <sub>j</sub>		20		pF
Temperature coefficient of φ <sub>e</sub>	I <sub>F</sub> = 20 mA	TKφ <sub>e</sub>		- 0.7		%/K
Angle of half intensity		φ		± 12		deg
Peak wavelength	I <sub>F</sub> = 100 mA	λ <sub>p</sub>		875		nm
Spectral bandwidth	I <sub>F</sub> = 100 mA	Δλ		80		nm
Temperature coefficient of λ <sub>p</sub>	I <sub>F</sub> = 100 mA	TKλ <sub>p</sub>		0.2		nm/K
Rise time	I <sub>F</sub> = 100 mA	t <sub>r</sub>		600		ns
	I <sub>F</sub> = 1 A	t <sub>r</sub>		300		ns
Fall time	I <sub>F</sub> = 100 mA	t <sub>f</sub>		600		ns
	I <sub>F</sub> = 1 A	t <sub>f</sub>		300		ns
Virtual source diameter		d		3.7		mm

**Note**

T<sub>amb</sub> = 25 °C, unless otherwise specified



# TSHA6200, TSHA6201, TSHA6202, TSHA6203

Infrared Emitting Diode, 875 nm, GaAlAs Vishay Semiconductors

TYPE DEDICATED CHARACTERISTICS							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 1 \text{ A}, t_p = 100 \mu\text{s}$	TSHA6200	$V_F$		2.8	3.5	V
		TSHA6201	$V_F$		2.8	3.5	V
		TSHA6202	$V_F$		2.8	3.5	V
		TSHA6203	$V_F$		2.8	3.5	V
Radiant intensity	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	TSHA6200	$I_e$	25	40	125	mW/sr
		TSHA6201	$I_e$	30	50	125	mW/sr
		TSHA6202	$I_e$	36	60	125	mW/sr
		TSHA6203	$I_e$	50	65	125	mW/sr
	$I_F = 1 \text{ A}, t_p = 100 \mu\text{s}$	TSHA6200	$I_e$	200	330		mW/sr
		TSHA6201	$I_e$	260	400		mW/sr
		TSHA6202	$I_e$	330	460		mW/sr
		TSHA6203	$I_e$	400	530		mW/sr
Radiant power	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	TSHA6200	$\phi_e$		22		mW
		TSHA6201	$\phi_e$		23		mW
		TSHA6202	$\phi_e$		24		mW
		TSHA6203	$\phi_e$		25		mW

**Note**

$T_{amb} = 25 \text{ }^\circ\text{C}$ , unless otherwise specified

**BASIC CHARACTERISTICS**

$T_{amb} = 25 \text{ }^\circ\text{C}$ , unless otherwise specified

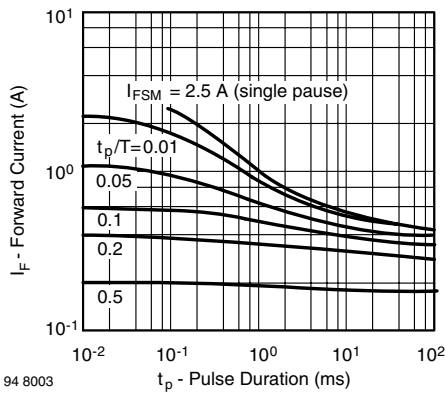


Fig. 3 - Pulse Forward Current vs. Pulse Duration

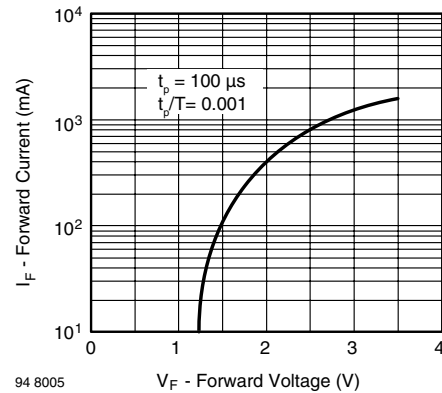


Fig. 4 - Forward Current vs. Forward Voltage

# TSHA6200, TSHA6201, TSHA6202, TSHA6203



Vishay Semiconductors Infrared Emitting Diode, 875 nm, GaAlAs

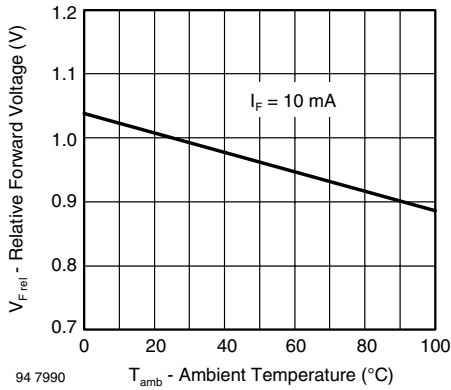


Fig. 5 - Relative Forward Voltage vs. Ambient Temperature

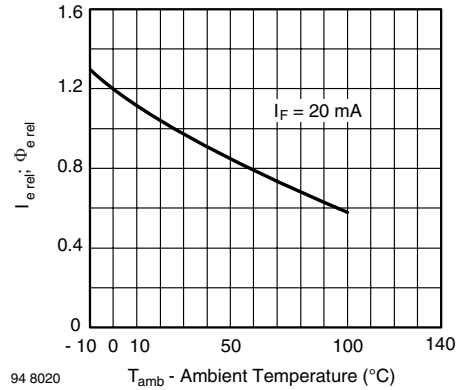


Fig. 8 - Relative Radiant Intensity/Power vs. Ambient Temperature

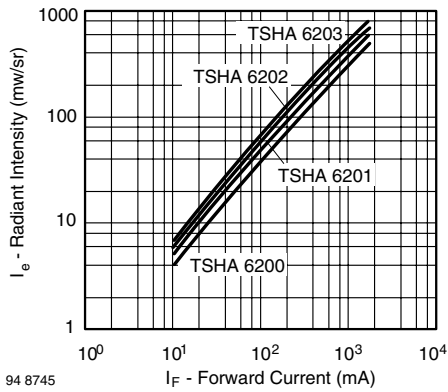


Fig. 6 - Radiant Intensity vs. Forward Current

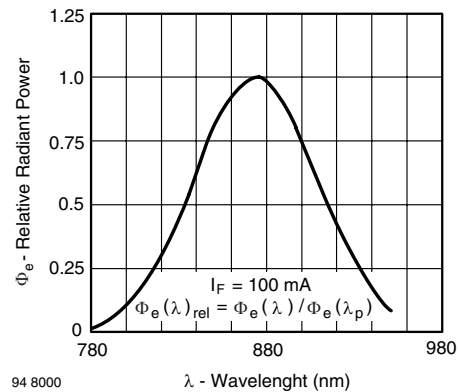


Fig. 9 - Relative Radiant Power vs. Wavelength

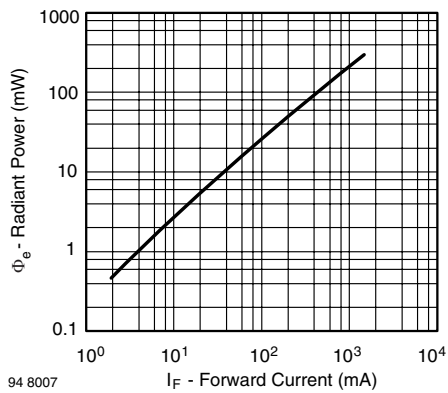


Fig. 7 - Radiant Power vs. Forward Current

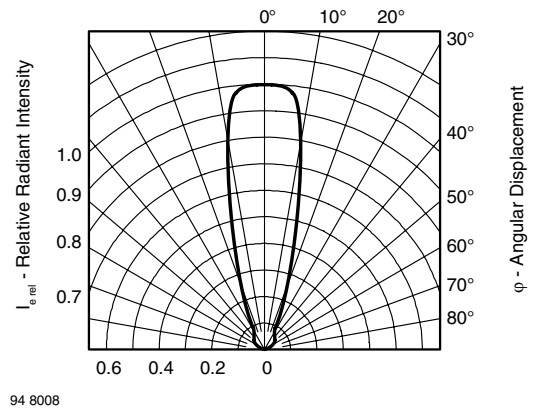


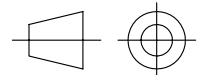
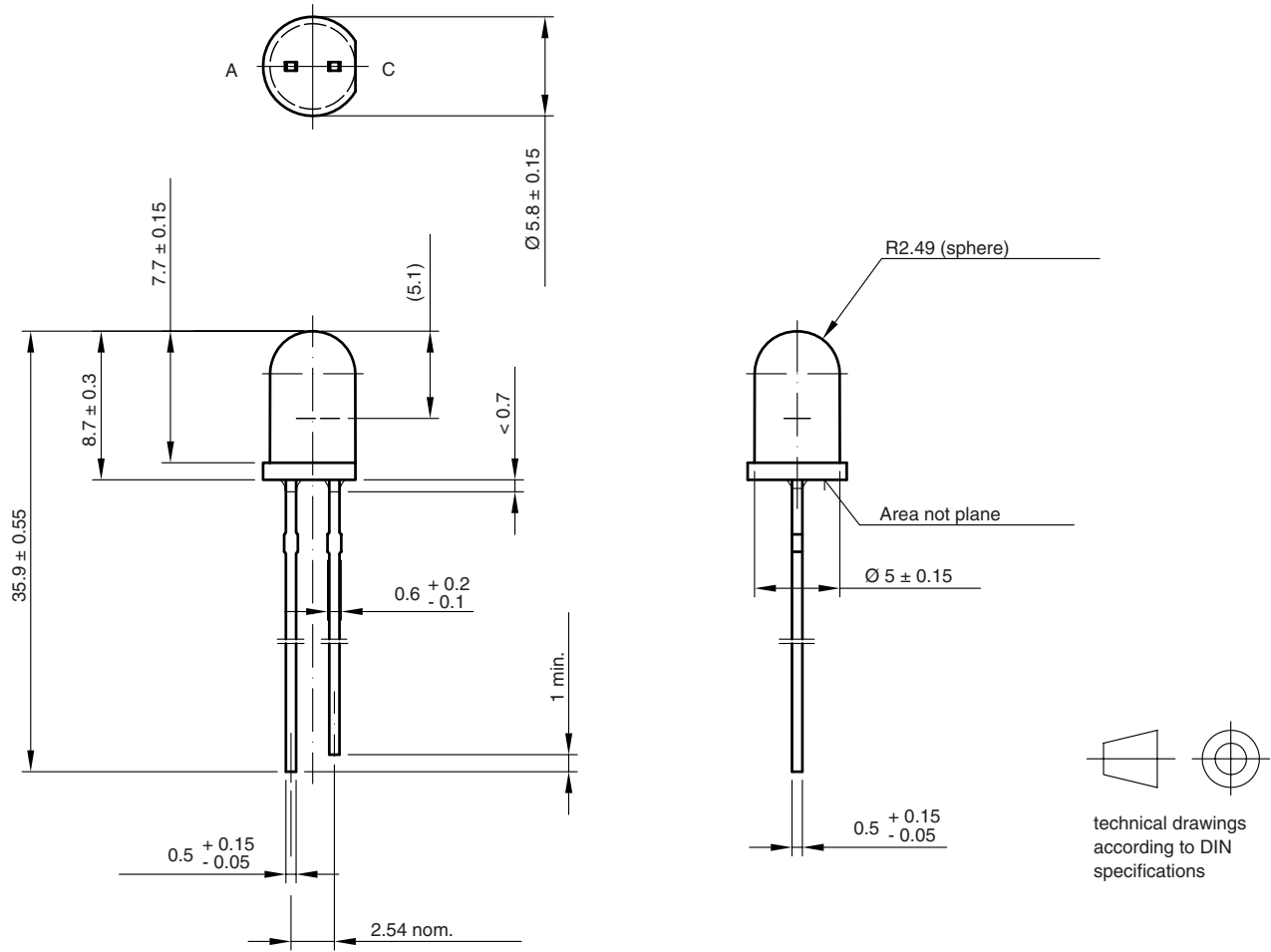
Fig. 10 - Relative Radiant Intensity vs. Angular Displacement



# TSHA6200, TSHA6201, TSHA6202, TSHA6203

Infrared Emitting Diode, 875 nm, GaAlAs Vishay Semiconductors

## PACKAGE DIMENSIONS in millimeters



technical drawings according to DIN specifications

Drawing-No.: 6.544-5259.04-4  
Issue: 8; 19.05.09  
96 12125



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